National Semiconductor

June 1989

54LS00/DM54LS00/DM74LS00 Quad 2-Input NAND Gates

General Description

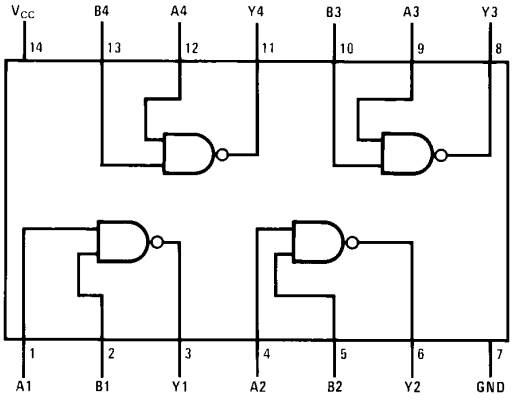
This device contains four independent gates each of which performs the logic NAND function.

Features

- Alternate Military/Aerospace device (54LS00) is available. Contact a National Semiconductor Sales Office/ Distributor for specifications.

Connection Diagram

Dual-In-Line Package



TL/F/6439–1

Order Number 54LS00DMQB, 54LS00FMQB, 54LS00LMQB, DM54LS00J, DM54LS00W, DM74LS00M or DM74LS00N
See NS Package Number E20A, J14A, M14A, N14A or W14B

Function Table

$Y = \overline{AB}$

Inputs		Output
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

H = High Logic Level
L = Low Logic Level

RRD-B30M105/Printed in U. S. A.

Absolute Maximum Ratings (Note)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage	7V
Input Voltage	7V
Operating Free Air Temperature Range	
DM54LS and 54LS	−55°C to +125°C
DM74LS	0°C to +70°C
Storage Temperature Range	−65°C to +150°C

Note: *The "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.*

Recommended Operating Conditions

Symbol	Parameter	DM54LS00			DM74LS00			Units
		Min	Nom	Max	Min	Nom	Max	
V_{CC}	Supply Voltage	4.5	5	5.5	4.75	5	5.25	V
V_{IH}	High Level Input Voltage	2			2			V
V_{IL}	Low Level Input Voltage			0.7			0.8	V
I_{OH}	High Level Output Current			−0.4			−0.4	mA
I_{OL}	Low Level Output Current			4			8	mA
T_A	Free Air Operating Temperature	−55		125	0		70	°C

Electrical Characteristics over recommended operating free air temperature range (unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ (Note 1)	Max	Units
V_I	Input Clamp Voltage	V_{CC} = Min, I_I = −18 mA				−1.5	V
V_{OH}	High Level Output Voltage	V_{CC} = Min, I_{OH} = Max, V_{IL} = Max	DM54	2.5	3.4		V
			DM74	2.7	3.4		
V_{OL}	Low Level Output Voltage	V_{CC} = Min, I_{OL} = Max, V_{IH} = Min	DM54		0.25	0.4	V
			DM74		0.35	0.5	
		I_{OL} = 4 mA, V_{CC} = Min	DM74		0.25	0.4	
I_I	Input Current @ Max Input Voltage	V_{CC} = Max, V_I = 7V				0.1	mA
I_{IH}	High Level Input Current	V_{CC} = Max, V_I = 2.7V				20	μA
I_{IL}	Low Level Input Current	V_{CC} = Max, V_I = 0.4V				−0.36	mA
I_{OS}	Short Circuit Output Current	V_{CC} = Max (Note 2)	DM54	−20		−100	mA
			DM74	−20		−100	
I_{CCH}	Supply Current with Outputs High	V_{CC} = Max			0.8	1.6	mA
I_{CCL}	Supply Current with Outputs Low	V_{CC} = Max			2.4	4.4	mA

Switching Characteristics at V_{CC} = 5V and T_A = 25°C (See Section 1 for Test Waveforms and Output Load)

Symbol	Parameter	R_L = 2 kΩ				Units
		C_L = 15 pF		C_L = 50 pF		
		Min	Max	Min	Max	
t_{PLH}	Propagation Delay Time Low to High Level Output	3	10	4	15	ns
t_{PHL}	Propagation Delay Time High to Low Level Output	3	10	4	15	ns

Note 1: All typicals are at V_{CC} = 5V, T_A = 25°C.

Note 2: Not more than one output should be shorted at a time, and the duration should not exceed one second.

FAIRCHILD SEMICONDUCTOR™

September 1983
Revised January 2005

MM74HC04
Hex Inverter

General Description

The MM74HC04 inverters utilize advanced silicon-gate CMOS technology to achieve operating speeds similar to LS-TTL gates with the low power consumption of standard CMOS integrated circuits.

The MM74HC04 is a triple buffered inverter. It has high noise immunity and the ability to drive 10 LS-TTL loads. The 74HC logic family is functionally as well as pin-out compatible with the standard 74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

Features

- Typical propagation delay: 8 ns
- Fan out of 10 LS-TTL loads
- Quiescent power consumption: 10 μW maximum at room temperature
- Low input current: 1 μA maximum

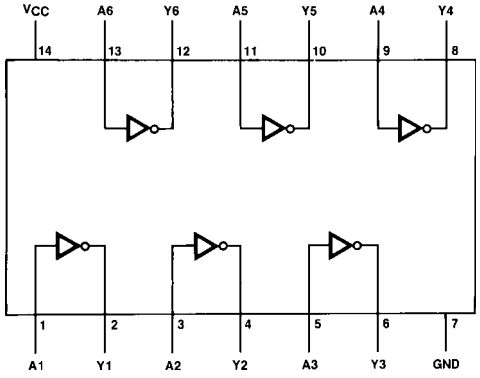
Ordering Code:

Order Number	Package Number	Package Description
MM74HC04M	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
MM74HC04M_NL		Pb-Free 14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
MM74HC04SJ	M14D	Pb-Free 14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
MM74HC04MTC	MTC14	14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide
MM74HC04MTC_NL	MTC14	Pb-Free 14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide
MM74HC04N	N14A	14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide
MM74HC04N_NL	N14A	Pb-Free 14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide

Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.
Pb-Free package per JEDEC J-STD-020B.

Connection Diagram

Pin Assignments for DIP, SOIC, SOP and TSSOP



Top View

Logic Diagram

1 of 6 Inverters

Absolute Maximum Ratings(Note 1)

(Note 2)

Supply Voltage (V_{CC})	−0.5 to +7.0V
DC Input Voltage (V_{IN})	−1.5 to V_{CC} +1.5V
DC Output Voltage (V_{OUT})	−0.5 to V_{CC} +0.5V
Clamp Diode Current (I_{IK}, I_{OK})	±20 mA
DC Output Current, per pin (I_{OUT})	±25 mA
DC V_{CC} or GND Current, per pin (I_{CC})	±50 mA
Storage Temperature Range (T_{STG})	−65°C to +150°C
Power Dissipation (P_D)	
(Note 3)	600 mW
S.O. Package only	500 mW
Lead Temperature (T_L)	
(Soldering 10 seconds)	260°C

Recommended Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temperature Range (T_A)	−40	+85	°C
Input Rise or Fall Times			
(t_r, t_f) V_{CC} = 2.0V		1000	ns
V_{CC} = 4.5V		500	ns
V_{CC} = 6.0V		400	ns

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: −12 mW/°C from 65°C to 85°C.

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	V_{CC}	T_A = 25°C	T_A = −40 to 85°C	T_A = −55 to 125°C	Units
				Typ	Guaranteed Limits		
V_{IH}	Minimum HIGH Level Input Voltage		2.0V		1.5	1.5	1.5	V
			4.5V		3.15	3.15	3.15	V
			6.0V		4.2	4.2	4.2	V
V_{IL}	Maximum LOW Level Input Voltage		2.0V		0.5	0.5	0.5	V
			4.5V		1.35	1.35	1.35	V
			6.0V		1.8	1.8	1.8	V
V_{OH}	Minimum HIGH Level Output Voltage	V_{IN} = V_{IL}						
		$\|I_{OUT}\| \leq$ 20 μA	2.0V	2.0	1.9	1.9	1.9	V
			4.5V	4.5	4.4	4.4	4.4	V
			6.0V	6.0	5.9	5.9	5.9	V
		V_{IN} = V_{IL}						
		$\|I_{OUT}\| \leq$ 4.0 mA	4.5V	4.2	3.98	3.84	3.7	V
		$\|I_{OUT}\| \leq$ 5.2 mA	6.0V	5.7	5.48	5.34	5.2	V
V_{OL}	Maximum LOW Level Output Voltage	V_{IN} = V_{IH}						
		$\|I_{OUT}\| \leq$ 20 μA	2.0V	0	0.1	0.1	0.1	V
			4.5V	0	0.1	0.1	0.1	V
			6.0V	0	0.1	0.1	0.1	V
		V_{IN} = V_{IH}						
		$\|I_{OUT}\| \leq$ 4.0 mA	4.5V	0.2	0.26	0.33	0.4	V
		$\|I_{OUT}\| \leq$ 5.2 mA	6.0V	0.2	0.26	0.33	0.4	V
I_{IN}	Maximum Input Current	V_{IN} = V_{CC} or GND	6.0V		±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current	V_{IN} = V_{CC} or GND I_{OUT} = 0 μA	6.0V		2.0	20	40	μA

Note 4: For a power supply of 5V ±10% the worst case output voltages (V_{OH}, and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC}=5.5V and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

AC Electrical Characteristics

V_{CC} = 5V, T_A = 25°C, C_L = 15 pF, $t_r = t_f$ = 6 ns

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL}, t_{PLH}	Maximum Propagation Delay		8	15	ns

AC Electrical Characteristics

V_{CC} = 2.0V to 6.0V, C_L = 50 pF, $t_r = t_f$ = 6 ns (unless otherwise specified)

Symbol	Parameter	Conditions	V_{CC}	T_A = 25°C	T_A = −40 to 85°C	T_A = −55 to 125°C	Units
				Typ	Guaranteed Limits		
t_{PHL}, t_{PLH}	Maximum Propagation Delay		2.0V	55	95	120	145	ns
			4.5V	11	19	24	29	ns
			6.0V	9	16	20	24	ns
t_{TLH}, t_{THL}	Maximum Output Rise and Fall Time		2.0V	30	75	95	110	ns
			4.5V	8	15	19	22	ns
			6.0V	7	13	16	19	ns
C_{PD}	Power Dissipation Capacitance (Note 5)	(per gate)		20				pF
C_{IN}	Maximum Input Capacitance			5	10	10	10	pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

FAIRCHILD SEMICONDUCTOR®

September 1983
Revised May 2005

MM74HC14
Hex Inverting Schmitt Trigger

General Description

The MM74HC14 utilizes advanced silicon-gate CMOS technology to achieve the low power dissipation and high noise immunity of standard CMOS, as well as the capability to drive 10 LS-TTL loads.

The 74HC logic family is functionally and pinout compatible with the standard 74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

Features

- Typical propagation delay: 13 ns
- Wide power supply range: 2–6V
- Low quiescent current: 20 μA maximum (74HC Series)
- Low input current: 1 μA maximum
- Fanout of 10 LS-TTL loads
- Typical hysteresis voltage: 0.9V at V_{CC} = 4.5V

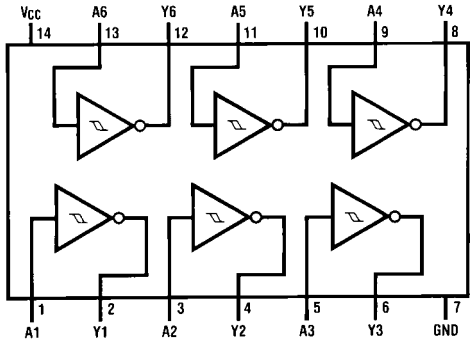
Ordering Code:

Order Number	Package Number	Package Description
MM74HC14M	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
MM74HC14MX_NL	M14A	Pb-Free 14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
MM74HC14SJ	M14D	Pb-Free 14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
MM74HC14MTC	MTC14	14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide
MM74HC14MTCX_NL	MTC14	Pb-Free 14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide
MM74HC14N	N14A	14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide
MM74HC14N_NL	N14A	Pb-Free 14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide

Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.
Pb-Free package per JEDEC J-STD-020B.

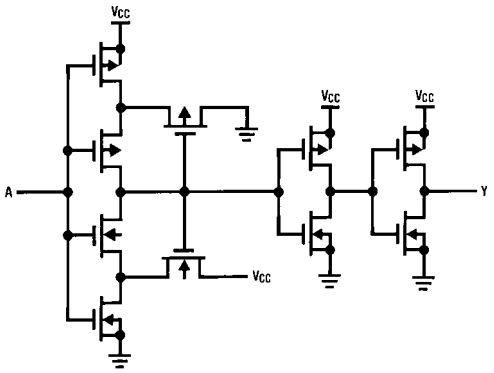
Connection Diagram

Pin Assignments for DIP, SOIC, SOP and TSSOP



Top View

Logic Diagram



Absolute Maximum Ratings(Note 1)

(Note 2)

Supply Voltage (V_{CC})	−0.5 to +7.0V
DC Input Voltage (V_{IN})	−1.5 to V_{CC} +1.5V
DC Output Voltage (V_{OUT})	−0.5 to V_{CC} +0.5V
Clamp Diode Current (I_{IK}, I_{OK})	±20 mA
DC Output Current, per pin (I_{OUT})	±25 mA
DC V_{CC} or GND Current, per pin (I_{CC})	±50 mA
Storage Temperature Range (T_{STG})	−65°C to +150°C
Power Dissipation (P_D)	
(Note 3)	600 mW
S.O. Package only	500 mW
Lead Temperature (T_L)	
(Soldering 10 seconds)	260°C

Recommended Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temperature Range (T_A)	−55	+125	°C

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: −12 mW/°C from 65°C to 85°C.

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	V_{CC}	T_A = 25°C	T_A = −40 to 85°C	T_A = −55 to 125°C	Units
				Typ	Guaranteed Limits		
V_{T+}	Positive Going	Minimum	2.0V	1.2	1.0	1.0	1.0	V
	Threshold Voltage		4.5V	2.7	2.0	2.0	2.0	V
			6.0V	3.2	3.0	3.0	3.0	V
		Maximum	2.0V	1.2	1.5	1.5	1.5	V
			4.5V	2.7	3.15	3.15	3.15	V
			6.0V	3.2	4.2	4.2	4.2	V
V_{T-}	Negative Going	Minimum	2.0V	0.7	0.3	0.3	0.3	V
	Threshold Voltage		4.5V	1.8	0.9	0.9	0.9	V
			6.0V	2.2	1.2	1.2	1.2	V
		Maximum	2.0V	0.7	1.0	1.0	1.0	V
			4.5V	1.8	2.2	2.2	2.2	V
			6.0V	2.2	3.0	3.0	3.0	V
V_H	Hysteresis Voltage	Minimum	2.0V	0.5	0.2	0.2	0.2	V
			4.5V	0.9	0.4	0.4	0.4	V
			6.0V	1.0	0.5	0.5	0.5	V
		Maximum	2.0V	0.5	1.0	1.0	1.0	V
			4.5V	0.9	1.4	1.4	1.4	V
			6.0V	1.0	1.5	1.5	1.5	V
V_{OH}	Minimum HIGH Level	V_{IN} = V_{IL}	2.0V	2.0	1.9	1.9	1.9	V
	Output Voltage	$\|I_{OUT}\|$ = 20 μA	4.5V	4.5	4.4	4.4	4.4	V
			6.0V	6.0	5.9	5.9	5.9	V
		V_{IN} = V_{IL}						
		$\|I_{OUT}\|$ = 4.0 mA	4.5V	4.2	3.98	3.84	3.7	V
		$\|I_{OUT}\|$ = 5.2 mA	6.0V	5.7	5.48	5.34	5.2	V
V_{OL}	Maximum LOW Level	V_{IN} = V_{IH}	2.0V	0	0.1	0.1	0.1	V
	Output Voltage	$\|I_{OUT}\|$ = 20 μA	4.5V	0	0.1	0.1	0.1	V
			6.0V	0	0.1	0.1	0.1	V
		V_{IN} = V_{IH}						
		$\|I_{OUT}\|$ = 4.0 mA	4.5V	0.2	0.26	0.33	0.4	V
		$\|I_{OUT}\|$ = 5.2 mA	6.0V	0.2	0.26	0.33	0.4	V
I_{IN}	Maximum Input Current	V_{IN} = V_{CC} or GND	6.0V		±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent	V_{IN} = V_{CC} or GND	6.0V		2.0	20	40	μA
	Supply Current	I_{OUT} = 0 μA						

Note 4: For a power supply of 5V ±10% the worst case output voltages (V_{OH}, and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC} = 5.5V and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

AC Electrical Characteristics

V_{CC} = 5V, T_A = 25°C, C_L = 15 pF, t_r = t_f = 6 ns

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL}, t_{PLH}	Maximum Propagation Delay		12	22	ns

AC Electrical Characteristics

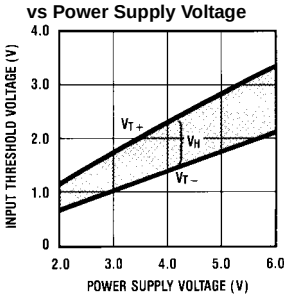
V_{CC} = 2.0V to 6.0V, C_L = 50 pF, t_r = t_f = 6 ns (unless otherwise specified)

Symbol	Parameter	Conditions	V_{CC}	T_A = 25°C	T_A = −40 to 85°C	T_A = −55 to 125°C		Units
				Typ	Guaranteed Limits			
t_{PHL}, t_{PLH}	Maximum Propagation Delay		2.0V	60	125	156	188	ns
			4.5V	13	25	31	38	ns
			6.0V	11	21	26	32	ns
t_{TLH}, t_{THL}	Maximum Output Rise and Fall Time		2.0V	30	75	95	110	ns
			4.5V	8	15	19	22	ns
			6.0V	7	13	16	19	ns
C_{PD}	Power Dissipation Capacitance (Note 5)	(per gate)		27				pF
C_{IN}	Maximum Input Capacitance			5	10	10	10	pF

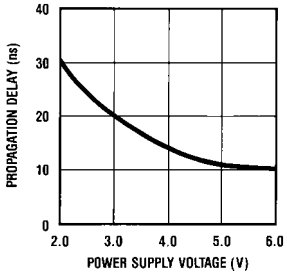
Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

Typical Performance Characteristics

Input Threshold, V_{T+}, V_{T-}, vs Power Supply Voltage



Propagation Delay vs Power Supply



November 2001

National Semiconductor

DS3658
Quad High Current Peripheral Driver

General Description

The DS3658 quad peripheral driver is designed for those applications where low operating power, high breakdown voltage, high output current and low output ON voltage are required. A unique input circuit combines TTL compatibility with high impedance. In fact, its extreme low input current allows it to be driven directly by a CMOS device.

The outputs are capable of sinking 600 mA each and offer a 70V breakdown. However, for inductive loads the output should be clamped to 35V or less to avoid latch-up during turn off (inductive fly back protection — refer AN-213). An on-chip clamp diode capable of handling 800 mA is provided at each output for this purpose. In addition, the DS3658 incorporates circuitry that guarantees glitch-free power up or down operation and a fail-safe feature which puts the output in a high impedance state when the input is open.

The molded package is specifically constructed to allow increased power dissipation over conventional packages. The four ground pins are directly connected to the device chip with a special cooper lead frame. When the quad driver is soldered into a PC board, the power rating of the device improves significantly.

Applications

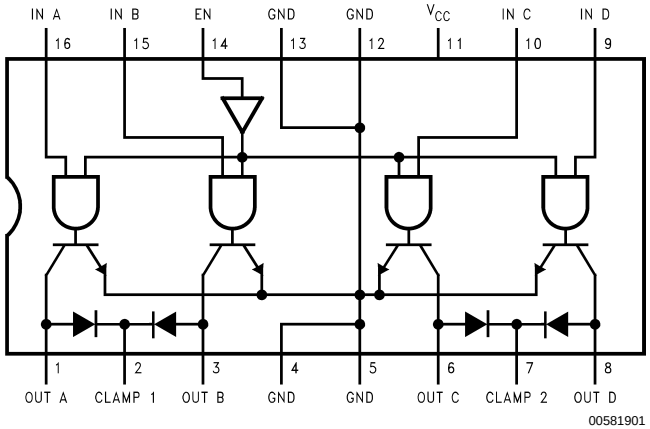
- Relay drivers
- Lamp drivers
- Solenoid drivers
- Hammer drivers
- Stepping motor drivers
- Triac drivers
- LED drivers
- High current, high voltage drivers
- Level translators
- Fiber optic LED drivers

Features

- Single saturated transistor outputs
- Low standby power, 10 mW typical
- High impedance TTL compatible inputs
- Outputs may be tied together for increased current capacity
- High output current
  — 600 mA per output
  — 2.4A per package
- No output latch-up at 35V
- Low output ON voltage (350 mV typ @ 600 mA)
- High breakdown voltage (70V)
- Open collector outputs
- Output clamp diodes for inductive fly back protection
- NPN inputs for minimal input currents (1 µA typical)
- Low operating power
- Standard 5V power supply
- Power up/down protection
- Fail safe operation
- 2W power package
- Pin-for-pin compatible with SN75437

Connection Diagram

Dual-In-Line Package



Top View
Order Number DS3658N
See NS Package Number N16E

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage	7V
Input Voltage	15V
Output Voltage	70V
Output Current	1.5A
Continuous Power Dissipation @ 25˚C Free-Air (Note 5)	2075 mW
Storage Temperature Range	−65˚C to +150˚C
Lead Temperature (Soldering, 4 sec.)	260˚C

Operating Conditions

	Min	Max	Units
Supply Voltage	4.75	5.25	V
Ambient Temperature	0	70	˚C

Electrical Characteristics (Notes 2, 3)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IH}	Input High Voltage		2.0			V
V_{IL}	Input Low Voltage				0.8	V
I_{IH}	Input High Current	V_{IN} = 5.25V, V_{CC} = 5.25V		1.0	1.0	µA
I_{IL}	Input Low Current	V_{IN} = 0.4V			±10	µA
V_{IK}	Input Clamp Voltage	I_I = −12 mA		−0.8	−1.5	V
V_{OL}	Output Low Voltage	I_L = 300 mA		0.2	0.4	V
		I_L = 600 mA (Note 4)		0.35	0.7	V
I_{CEX}	Output Leakage Current	V_{CE} = 70V, V_{IN} = 0.8V			100	µA
V_F	Diode Forward Voltage	I_F = 800 mA		1.0	1.6	V
I_R	Diode Leakage Current	V_R = 70V			100	µA
I_{CC}	Supply Current	All Inputs High		60	85	mA
		All Inputs Low		2	4	mA

Switching Characteristics (Note 2)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
t_{PHL}	Turn On Delay	R_L = 60Ω, V_L = 30V		226	500	ns
t_{PLH}	Turn Off Delay	R_L = 60Ω, V_L = 30V		2430	8000	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the 0˚C to +70˚C temperature range and the 4.75V to 5.25V power supply range. All typical values are for T_A = 25˚C and V_{CC} = 5.0V.

Note 3: All currents into device pins are shown as positive, all currents out of device pins are shown as negative, all voltages are referenced to ground, unless otherwise specified. All values shown as max or min are so classified on absolute value basis.

Note 4: All sections of this quad circuit may conduct rated current simultaneously, however, power dissipation averaged over a short interval of time must fall within specified continuous dissipation ratings.

Note 5: For operation over 25˚ free-air temperature, derate linearly to 1328 mW @ 70˚C @ the rate of 16.6 mW/˚C.

Truth Table

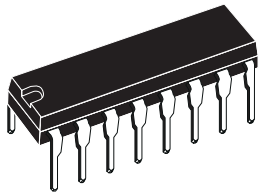
IN	EN	OUT
H	H	L
L	H	Z
H	L	Z
L	L	Z

H = High state
L = Low state
Z = High impedance state

ULN2001A-ULN2002A
ULN2003A-ULN2004A

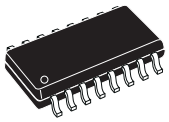
SEVEN DARLINGTON ARRAYS

- SEVEN DARLINGTONS PER PACKAGE
- OUTPUT CURRENT 500mA PER DRIVER (600mA PEAK)
- OUTPUT VOLTAGE 50V
- INTEGRATED SUPPRESSION DIODES FOR INDUCTIVE LOADS
- OUTPUTS CAN BE PARALLELED FOR HIGHER CURRENT
- TTL/CMOS/PMOS/DTL COMPATIBLE INPUTS
- INPUTS PINNED OPPOSITE OUTPUTS TO SIMPLIFY LAYOUT



DIP16

ORDERING NUMBERS: ULN2001A/2A/3A/4A



SO16

ORDERING NUMBERS: ULN2001D/2D/3D/4D

DESCRIPTION

The ULN2001A, ULN2002A, ULN2003 and ULN2004A are high voltage, high current darlington arrays each containing seven open collector darlington pairs with common emitters. Each channel rated at 500mA and can withstand peak currents of 600mA. Suppression diodes are included for inductive load driving and the inputs are pinned opposite the outputs to simplify board layout.

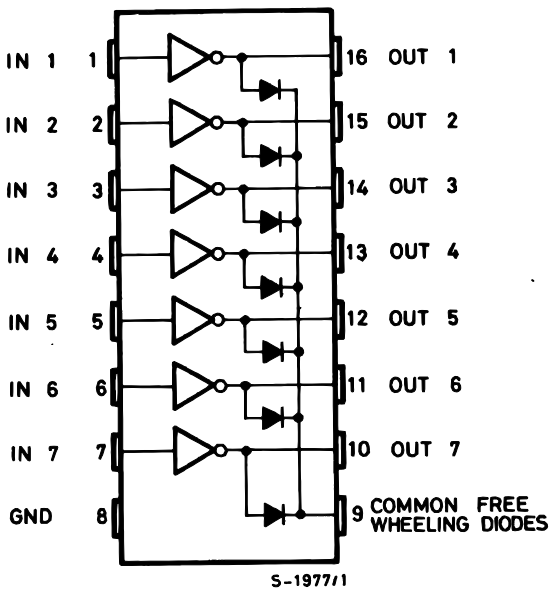
The four versions interface to all common logic families :

ULN2001A	General Purpose, DTL, TTL, PMOS, CMOS
ULN2002A	14-25V PMOS
ULN2003A	5V TTL, CMOS
ULN2004A	6–15V CMOS, PMOS

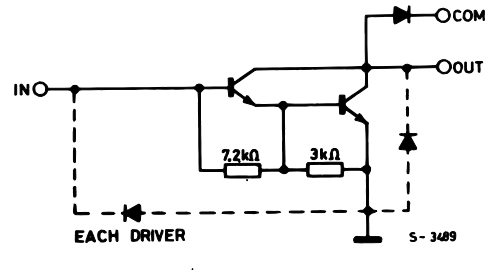
These versatile devices are useful for driving a wide range of loads including solenoids, relays DC motors, LED displays filament lamps, thermal printheads and high power buffers.

The ULN2001A/2002A/2003A and 2004A are supplied in 16 pin plastic DIP packages with a copper leadframe to reduce thermal resistance. They are available also in small outline package (SO-16) as ULN2001D/2002D/2003D/2004D.

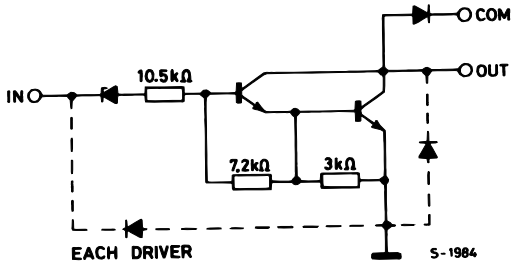
PIN CONNECTION



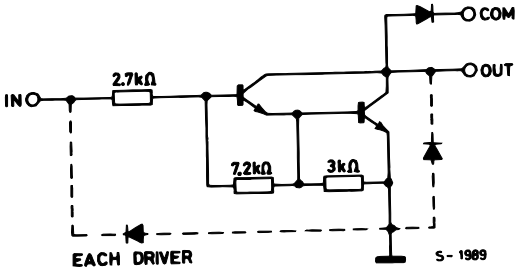
SCHEMATIC DIAGRAM



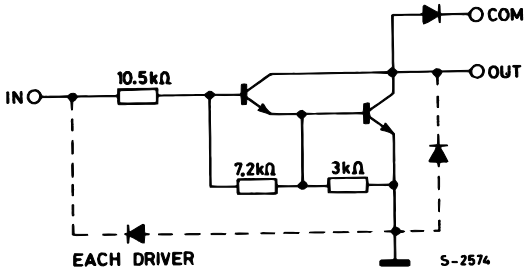
Series ULN-2001A
(each driver)



Series ULN-2002A
(each driver)



Series ULN-2003A
(each driver)



Series ULN-2004A
(each driver)

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_o	Output Voltage	50	V
V_{in}	Input Voltage (for ULN2002A/D - 2003A/D - 2004A/D)	30	V
I_c	Continuous Collector Current	500	mA
I_b	Continuous Base Current	25	mA
T_{amb}	Operating Ambient Temperature Range	– 20 to 85	°C
T_{stg}	Storage Temperature Range	– 55 to 150	°C
T_j	Junction Temperature	150	°C

THERMAL DATA

Symbol	Parameter		DIP16	SO16	Unit
$R_{th\ j\text{-}amb}$	Thermal Resistance Junction-ambient	Max.	70	120	°C/W

ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	Fig.
I_{CEX}	Output Leakage Current	V_{CE} = 50V T_{amb} = 70°C, V_{CE} = 50V T_{amb} = 70°C for ULN2002A V_{CE} = 50V, V_i = 6V for ULN2004A V_{CE} = 50V, V_i = 1V			50 100 500 500	µA µA µA µA	1a 1a 1b 1b
$V_{CE(sat)}$	Collector-emitter Saturation Voltage	I_C = 100mA, I_B = 250µA I_C = 200 mA, I_B = 350µA I_C = 350mA, I_B = 500µA		0.9 1.1 1.3	1.1 1.3 1.6	V V V	2 2 2
$I_{i(on)}$	Input Current	for ULN2002A, V_i = 17V for ULN2003A, V_i = 3.85V for ULN2004A, V_i = 5V V_i = 12V		0.82 0.93 0.35 1	1.25 1.35 0.5 1.45	mA mA mA mA	3 3 3 3
$I_{i(off)}$	Input Current	T_{amb} = 70°C, I_C = 500µA	50	65		µA	4
$V_{i(on)}$	Input Voltage	V_{CE} = 2V for ULN2002A I_C = 300mA for ULN2003A I_C = 200mA I_C = 250mA I_C = 300mA for ULN2004A I_C = 125mA I_C = 200mA I_C = 275mA I_C = 350mA			 13 2.4 2.7 3 5 6 7 8	V	5
h_{FE}	DC Forward Current Gain	for ULN2001A V_{CE} = 2V, I_C = 350mA	1000				2
C_i	Input Capacitance			15	25	pF	
t_{PLH}	Turn-on Delay Time	0.5 V_i to 0.5 V_o		0.25	1	µs	
t_{PHL}	Turn-off Delay Time	0.5 V_i to 0.5 V_o		0.25	1	µs	
I_R	Clamp Diode Leakage Current	V_R = 50V T_{amb} = 70°C, V_R = 50V			50 100	µA µA	6 6
V_F	Clamp Diode Forward Voltage	I_F = 350mA		1.7	2	V	7

Figure 8: Collector Current versus Input Current

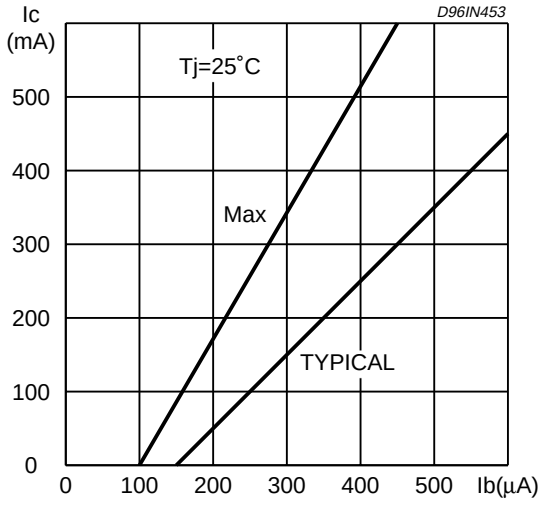


Figure 9: Collector Current versus Saturation Voltage

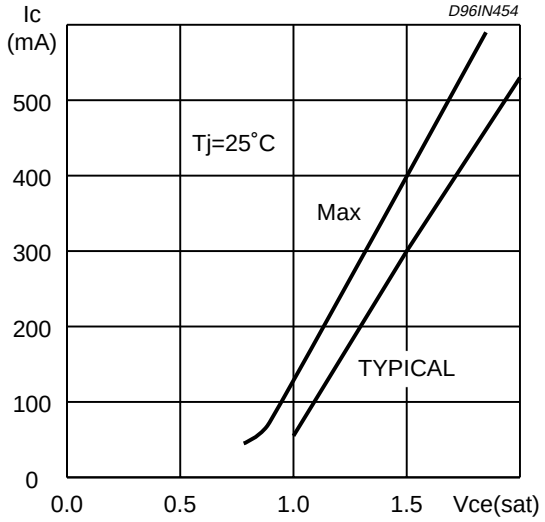


Figure 10: Peak Collector Current versus Duty Cycle

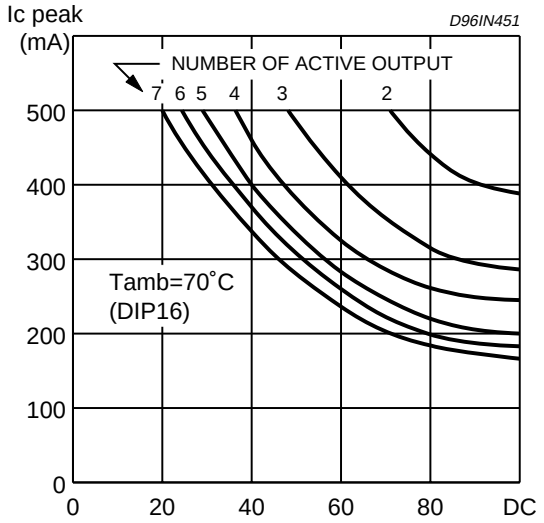


Figure 11: Peak Collector Current versus Duty Cycle